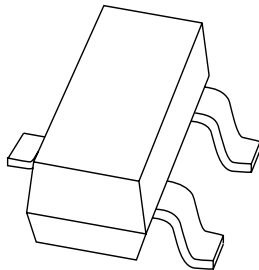


DATA SHEET



BFS20

NPN medium frequency transistor

Product data sheet
Supersedes data of 2004 Jan 5

2004 Feb 05

NPN medium frequency transistor

BFS20

FEATURES

- $I_{C(max)} = 25 \text{ mA}$
- $V_{CEO(max)} = 20 \text{ V}$
- Very low feedback capacitance (typ. 350 fF).

APPLICATIONS

- IF and VHF thick and thin-film circuit applications.

DESCRIPTION

NPN medium frequency transistor in a SOT23 plastic package.

MARKING

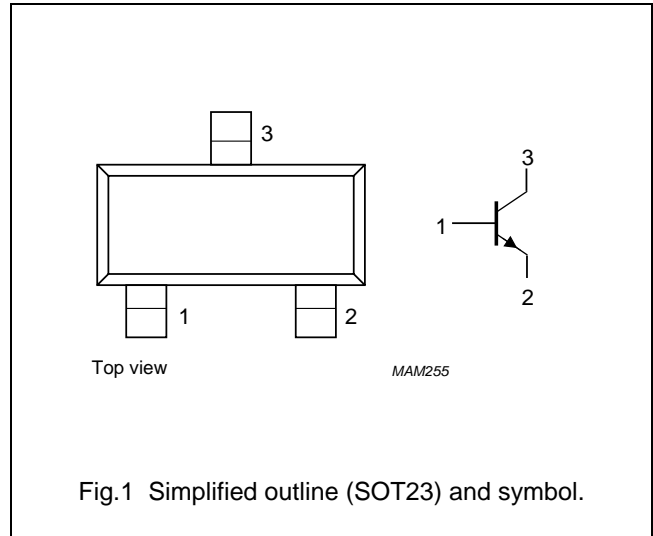
TYPE NUMBER	MARKING CODE ⁽¹⁾
BFS20	G1*

Note

- * = p : Made in Hong Kong.
 * = t : Made in Malaysia.
 * = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BFS20	-	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	-	30	V
V_{CEO}	collector-emitter voltage	open base	-	20	V
V_{EBO}	emitter-base voltage	open collector	-	4	V
I_C	collector current (DC)		-	25	mA
I_{CM}	peak collector current		-	25	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25 \text{ }^\circ\text{C}$; note 1	-	250	mW
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		-65	+150	$^\circ\text{C}$

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN medium frequency transistor

BFS20

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CB0}	collector-base cut-off current	$I_E = 0; V_{CB} = 20\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 20\text{ V}; T_j = 100\text{ °C}$	–	–	10	μA
I_{EBO}	emitter-base cut-off current	$I_C = 0; V_{EB} = 4\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 7\text{ mA}; V_{CE} = 10\text{ V}$	40	85	–	
V_{BE}	base-emitter voltage	$I_C = 7\text{ mA}; V_{CE} = 10\text{ V}$	–	740	900	mV
C_c	collector capacitance	$I_E = I_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	1	–	pF
C_{re}	feedback capacitance	$I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	350	–	fF
f_T	transition frequency	$I_C = 5\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	275	450	–	MHz

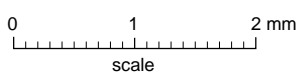
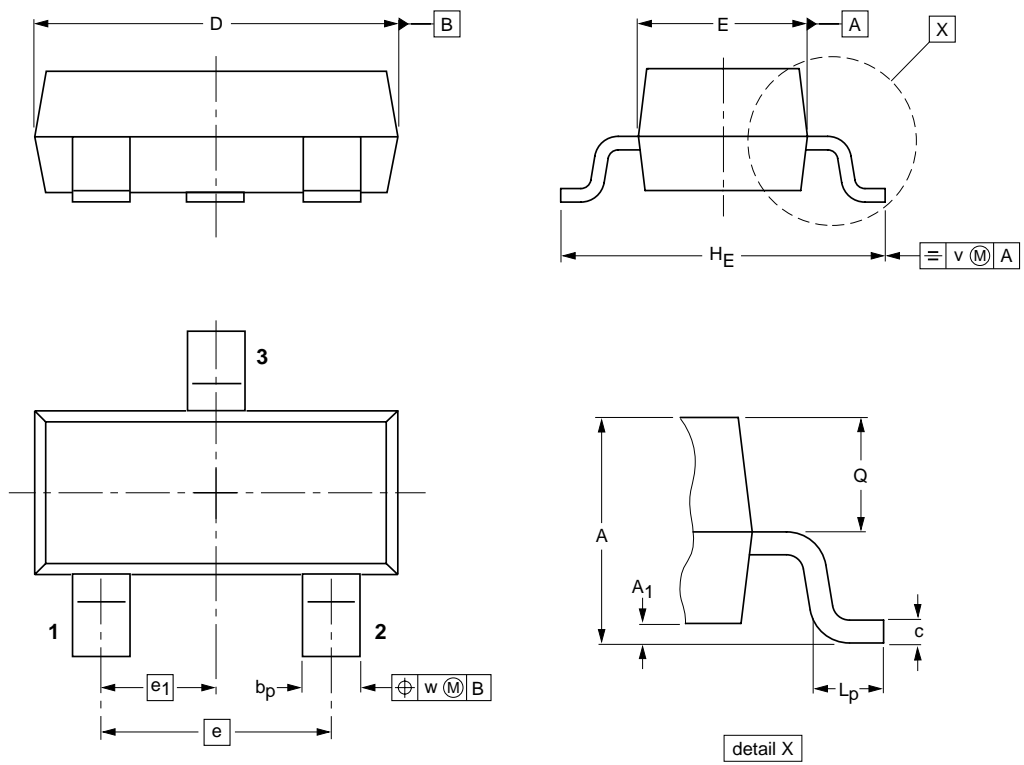
NPN medium frequency transistor

BFS20

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16